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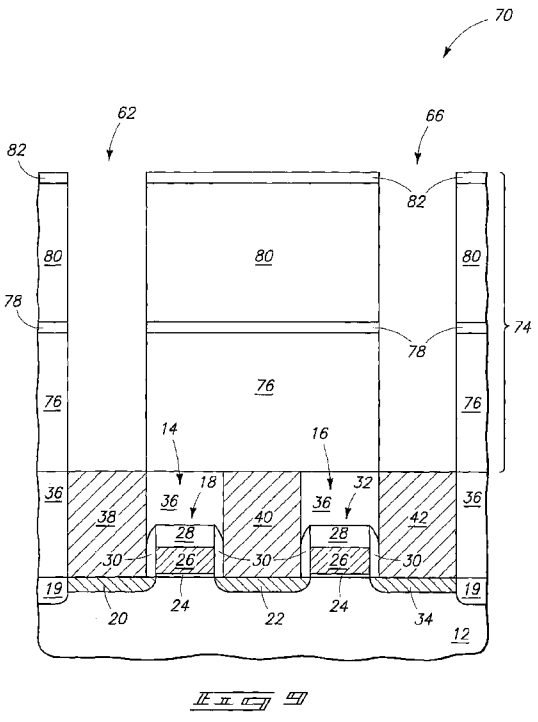
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(54) **Title**: SEMICONDUCTOR CONSTRUCTIONS, AND METHODS OF FORMING SEMICONDUCTOR CONSTRUCTIONS



(57) **Abstract**: Some embodiments include methods of forming semiconductor constructions. Oxide is formed over a substrate, and first material is formed over the oxide. Second material is formed over the first material. The second material may be one or both of polycrystalline and amorphous silicon. A third material is formed over the second material. A pattern is transferred through the first material, second material, third material, and oxide to form openings. Capacitors may be formed within the openings. Some embodiments include semiconductor constructions in which an oxide is over a substrate, a first material is over the oxide, and a second material containing one or both of polycrystalline and amorphous silicon is over the first material. Third, fourth and fifth materials are over the second material. An opening may extend through the oxide; and through the first, second, third, fourth and fifth materials.

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